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U.S. PATENT & TRADEMARK OFFICE

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Attorney Docket No. 33851/42502 DIV
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s):	James D. Beasom	Conf. No.:	7103
Serial No.:	10/685,972	Art Unit:	2812
Filed:	October 15, 2003	Examiner:	Mulpuri, Savitri
For:	REDUCED MASK COUNT BURIED LAYER		

AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In response to Official Office Action dated April 11,2005, please amend the subject application as follows:

IN THE CLAIMS

Please see the Claim Summary Document attached hereto.

REMARKS

In the official Office Action dated April 11, 2005, claims 1-17 and 57-64 are rejected either as anticipated under 35 U.S.C. 102b by Beasom U.S. Patent 5,652,153 ("Beasom '153") or obvious under 35 U.S.C. 103 further in view of Pendharkar et al. 02/0053685 and Park et al. U.S. Patent 5,880,014. These rejections were respectively traversed.

Claim 1 is directed specifically to a method of fabricating a semiconductor device comprising the steps of: a) forming a nonselective N+ type buried layer comprising a first majority dopant and having a first coefficient of diffusion; b) forming a selective P+ type buried layer comprising a second majority dopant and having a coefficient of diffusion greater than the first coefficient of diffusion.

The rejection identifies "a non-selective N type buried layer '12' . . . and a selective P type dash buried layer '36' . . ." Applicant does not disagree that 12 is a nonselective N-type layer and 36 is a selective P type layer and that both of them are below the top surface of the substrate. They are not the buried layer which applicant's invention is improvement over. Applicant's buried layers are specifically N+ and P+ buried layers which are highly doped